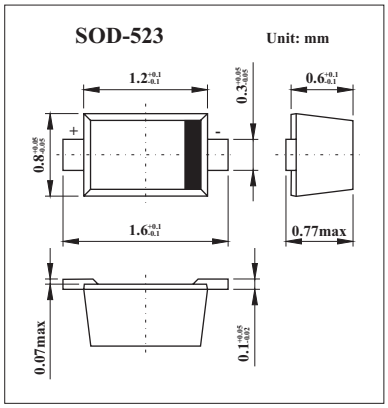
Silicon Epitaxial Trench Pin Diode

HVC135



Features

- Adopting the trench structure improves low capacitance.(C=0.6pF max)
- Low forward resistance. (rf=2.0Ω max)
- Low operation current.

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Peak reverse voltage	V_{RM}	65	V
Reverse voltage	V_R	60	V
Forward current	I_F	100	mA
Power dissipation	P_d	150	mW
Junction temperature	T_j	125	℃
Storage temperature	T_{stg}	-55 to +125	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current	I_R	V_R = 60 V			0.1	μA
Reverse voltage	V_F	I_F = 2 mA			0.9	V
Capacitance	C	V_R = 1 V, f = 1 MHz			0.6	pF
Forward resistance	rf	I_F = 2 mA, f = 100 MHz			2.0	Ω
ESD-Capability *1		C =200pF, Both forward and reverse direction 1 pulse	100			V

Note

1. Failure criterion ; I_R > 100 nA at V_R = 60V.

Marking

Marking	P5